



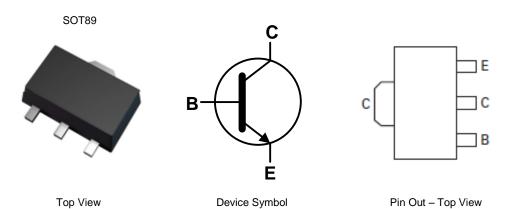
32V NPN SURFACE MOUNT TRANSISTOR IN SOT89

Features

- BV_{CEO} > 32V
- Maximum Continuous Current I_C = 1A
- Epitaxial Planar Die Construction
- Complementary PNP Type Available (2DB1132)
- Ideally Suited for Automated Assembly Processes
- Ideal for Medium Power Switching or Amplification Applications
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT89
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish @3
- Weight: 0.055 grams (Approximate)



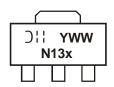
Ordering Information (Note 4)

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
2DD1664P-13	N13P	13	12	2,500
2DD1664Q-13	N13Q	13	12	2,500
2DD1664R-13	N13R	13	12	2,500

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



Oll = Manufacturer's Marking
N13x = Product Type Marking Code:
Where N13P = 2DD1664P

N13Q = 2DD1664Q N13Q = 2DD1664Q N13R = 2DD1664R

YWW = Date Code Marking Y = Last Digit of Year (ex: 9 = 2019) WW = Week Code (01 to 53)



Absolute Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	40	V
Collector-Emitter Voltage	V _{CEO}	32	V
Emitter-Base Voltage	V _{EBO}	6	V
Continuous Collector Current	Ic	1	Α
Peak Pulse Current (Note 6)	I _{CM}	2	Α

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 5)		1		
Power Dissipation	(Note 6)	P_{D}	1.5	W	
	(Note 7)		2.0	1	
	(Note 5)		125	°C/W	
Thermal Resistance, Junction to Ambient Air	(Note 6)	$R_{\theta JA}$	83		
	(Note 7)		60		
Thermal Resistance, Junction to Case	(Note 5)	R ₀ JC	18	°C/W	
Thermal Resistance, Junction to Lead (Note 8)		$R_{\theta JL}$	22	°C/W	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C	

ESD Ratings (Note 9)

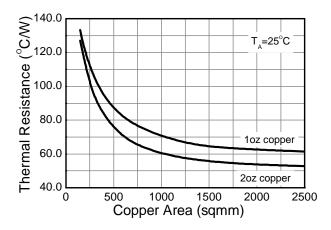
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

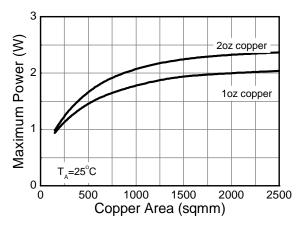
Notes:

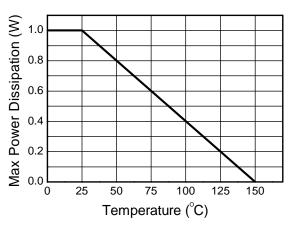
- 5. For a device mounted with the exposed collector pad on 15mm x 15mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 6. Same as note (5), except the device is mounted on 25mm x 25mm 1oz copper.
- 7. Same as note (5), except the device is mounted on 50mm x 50mm 1oz copper.
- 8. Thermal resistance from junction to solder-point (on the exposed collector pad).
- 9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

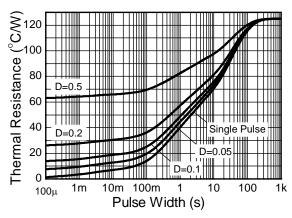


Thermal Characteristics and Derating Information



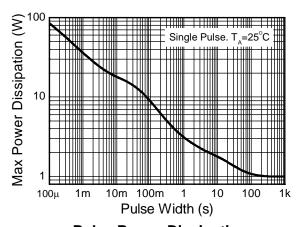






Derating Curve

Transient Thermal Impedance



Pulse Power Dissipation



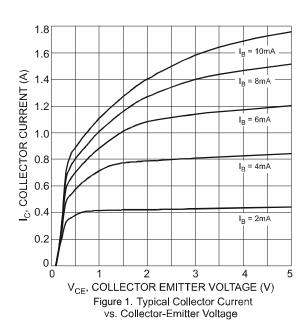
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

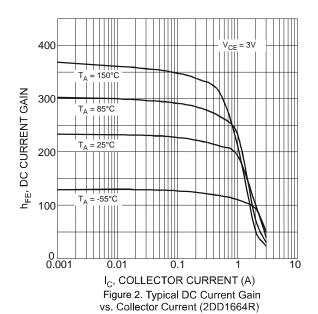
Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage		BV _{CBO}	40	_	_	V	$I_C = 100\mu A$
Collector-Emitter Breakdown Voltage	e (Note 10)	BV _{CEO}	32	_	_	V	I _C = 10mA
Emitter-Base Breakdown Voltage		BV _{EBO}	6	_	_	V	$I_{E} = 100 \mu A$
Collector-Emitter Cut-Off Current		I _{CES}	_	_	100	nA	V _{CE} = 32V
Collector-Base Cut-Off Current		I _{CBO}	_	_	100	nA	V _{CB} = 36V
Base-Emitter Cut-Off Current		I _{EBO}	_	_	100	nA	$V_{EB} = 6V$
Static Forward Current Transfer	2DD1664P		82		180		
Ratio (Note 10)	2DD1664Q	h _{FE}	120	_	270		$I_C = 100 \text{mA}, V_{CE} = 3V$
Italio (Note 10)	2DD1664R		180		390		
Collector-Emitter Saturation Voltage (Note 10)		V _{CE(SAT)}	_	120	400	mV	$I_C = 500 \text{mA}, I_B = 50 \text{mA}$
Transition Frequency		f_T		280		MHz	$I_E = 50 \text{mA}, V_{CE} = 5 \text{V}, f = 30 \text{MHz}$
Output Capacitance		C_ob	_	10	_	pF	$I_E = 0A$, $V_{CB} = 10V$, $f = 1MHz$

Note:

10. Measured under pulsed conditions. Pulse width = 300µs. Duty cycle ≤ 2%.

Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)







Typical Electrical Characteristics (continued) (@TA = +25°C, unless otherwise specified.)

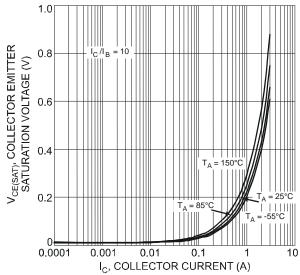


Figure 3. Typical Collector-Emitter Saturation Voltage vs. Collector Current

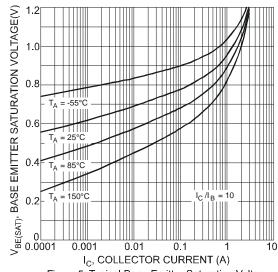


Figure 5. Typical Base-Emitter Saturation Voltage vs. Collector Current

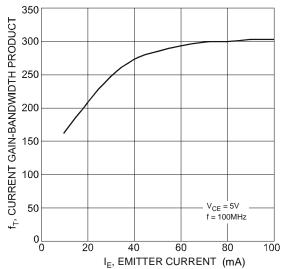


Figure 7. Typical Gain-Bandwidth Product vs. Emitter Current

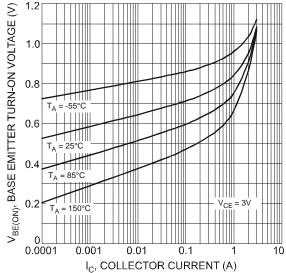


Figure 4. Typical Base-Emitter Turn-On Voltage vs. Collector Current

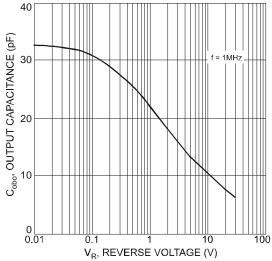


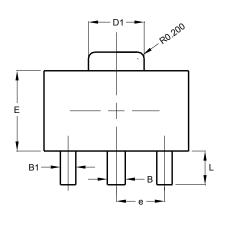
Figure 6. Typical Output Capacitance Characteristics

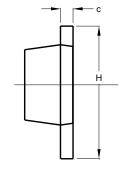


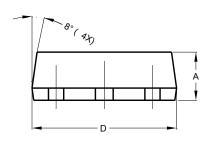
Package Outline Dimensions

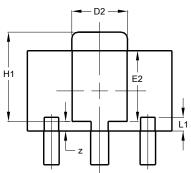
Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT89







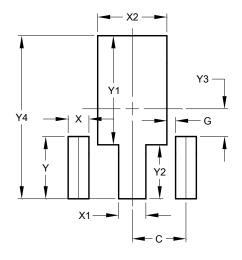


SOT89						
Dim	Min	Max	Тур			
Α	1.40	1.60	1.50			
В	0.50	0.62	0.56			
B1	0.42	0.54	0.48			
C	0.35	0.43	0.38			
D	4.40	4.60	4.50			
D1	1.62	1.83	1.733			
D2	1.61	1.81	1.71			
Е	2.40	2.60	2.50			
E2	2.05	2.35	2.20			
е	1	-	1.50			
Н	3.95	4.25	4.10			
H1	2.63	2.93	2.78			
L	0.90	1.20	1.05			
L1	0.327	0.527	0.427			
Z	0.20	0.40	0.30			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT89



Dimensions	Value
Dimensions	(in mm)
С	1.500
G	0.244
Х	0.580
X1	0.760
X2	1.933
Υ	1.730
Y1	3.030
Y2	1.500
Y3	0.770
Y4	4.530



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